Panasonic

MOS FET FCAB21350L1

FCAB21350L1 Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

Features

- Low source-source ON resistance:Rss(on) typ. = $2.2 \text{ m}\Omega(\text{VGS} = 3.8 \text{ V})$
- CSP(Chip Size Package)
- · RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 3M

Packaging

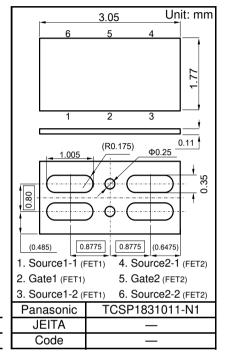
Embossed type (Thermo-compression sealing) : 1 000 pcs / reel (standard)

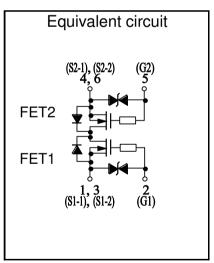
■ Absolute Maximum Ratings Ta = 25 °C								
Parameter		Symbol	Rating	Unit				
Source-source Voltage		VSS	12	V				
Gate-source Voltage		VGS	±8	V				
Source Current	DC ^{*1}	IS1	12	А				
	DC *2	IS2	27	А				
	Pulse *3	ISp	120	Α				
Total Power Dissipation	DC ^{*1}	PD1	0.45	W				
	DC ^{*2}	PD2	2.1	W				
Channel Temperature		Tch	150	°C				
Storage Temperature Range		Tstg	-55 to +150	°C				
Thermal Resistance (ch-a)	DC ^{*1}	Rth1	278	°C/W				
	DC ^{*2}	Rth2	59	°C/W				
Note *1 Maximuted are ED4 beauty (OE 4 many OE 4 many to 0 many)								

Note *1 Mounted on FR4 board ($25.4 \text{ mm} \times 25.4 \text{ mm} \times t1.0 \text{ mm}$) using the minimum recommended pad size (36μ m Copper).

*2 Mounted on Ceramic substrate (70 mm \times 70 mm \times t1.0 mm).

*3 t = 10 μ s, Duty Cycle \leq 1 %







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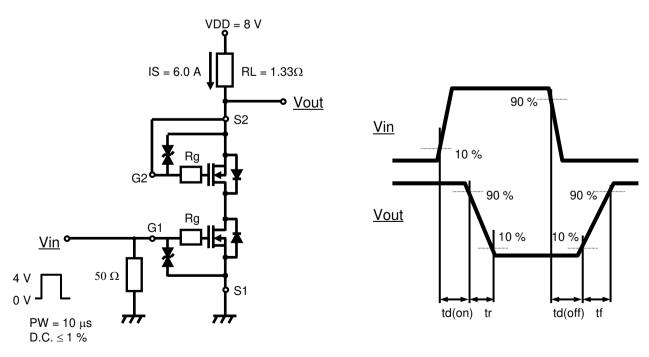
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	12			V	
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μA	
Gate-source Leakage Current	IGSS	$VGS = \pm 8 V, VSS = 0 V$			±10	μA	
	1000	$VGS = \pm 5 V, VSS = 0 V$			±1.0	μΑ	
Gate-source Threshold Voltage	Vth	IS = 1.41 mA, VSS = 10 V	0.35	0.90	1.40	V	
Source-source On-state Resistance	RSS(on)1	IS = 6.0 A, VGS = 4.5 V	1.55	2.1	2.75		
	RSS(on)2	IS = 6.0 A, VGS = 3.8 V	1.6	2.2	2.85	mΩ	
	RSS(on)3	IS = 6.0 A, VGS = 3.1 V	1.65	2.4	3.95		
	RSS(on)4	IS = 6.0 A, VGS = 2.5 V	1.9	3.1	6.1		
Body Diode Forward Voltage	VF(s-s)	IF = 6.0 A, VGS = 0 V		0.8	1.2	V	
Input Capacitance ^{*1}	Ciss			4650		pF	
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 KHz		580			
Reverse Transfer Capacitance ^{*1}	Crss			530			
Turn-on delay Time ^{*1,*2}	td(on)	VDD = 8 V, VGS = 0 to 4.0 V		1.2		μS	
Rise Time ^{*1,*2}	tr	IS = 6.0 A		2.3			
Turn-off delay Time *1,*2	td(off)	VDD = 8 V, VGS = 4.0 to 0 V		9		μS	
Fall Time ^{*1,*2}	tf	IS = 6.0 A		5.0			
Total Gate Charge ¹	Qg	VDD = 8 V		43			
Gate-source Charge ^{*1}	Qgs	VGS = 0 to 4.0 V,		10		nC	
Gate-drain Charge ¹	Qgd	IS = 6.0 A		10			

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

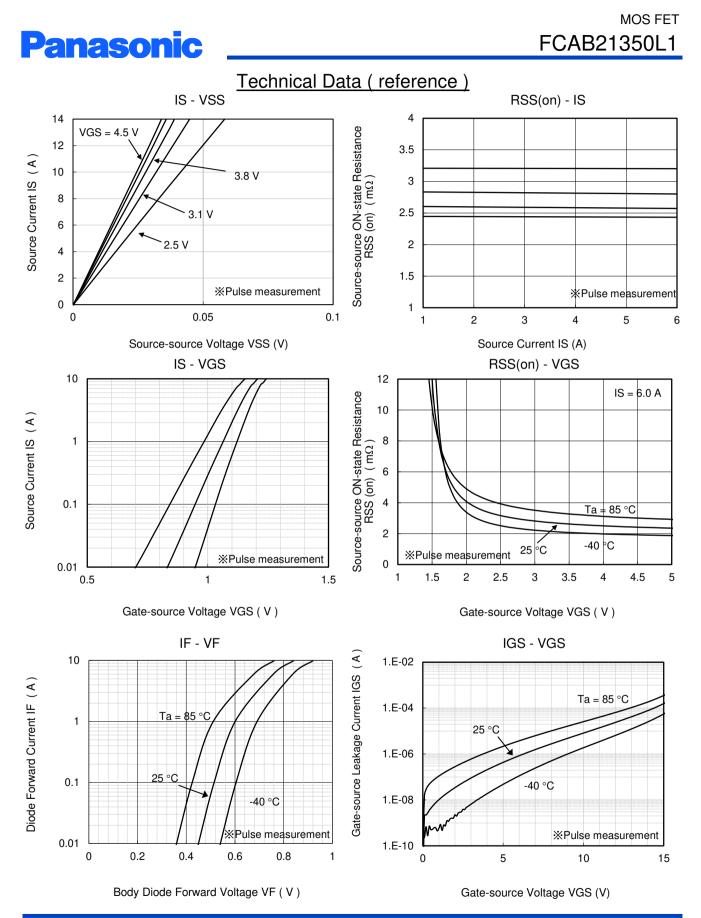
*1 Guaranteed by design, not subject to production testing

*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

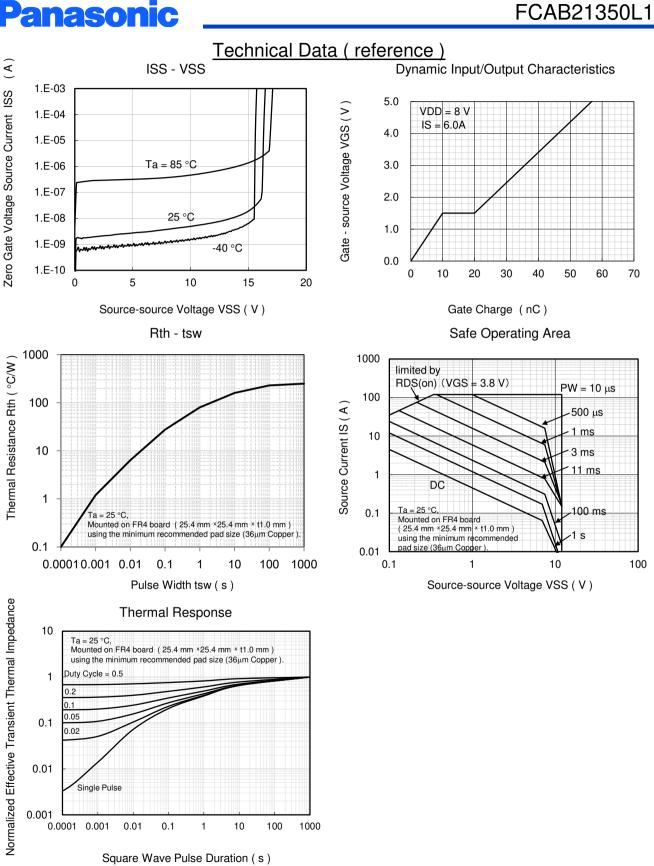


Note2 : Measurement circuit

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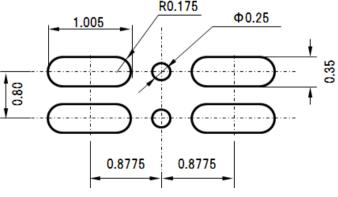
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 $\textbf{3.05} \pm 0.04$ 6 5 4 1.77 ± 0.04 Ο 3 1 2 0.11 -0.05 (R0.175) Φ0.25 1.005 0.35 Z 0.80 ·· _ · _ 0.8775 0.8775 (0.485) (0.6475)

■ Land Pattern (Reference)

R0.175 Φ0.25

Established : 2015-10-23 :####-##-## Revised





■ Outline (TCSP1831011-N1)

Unit: mm

Unit: mm

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